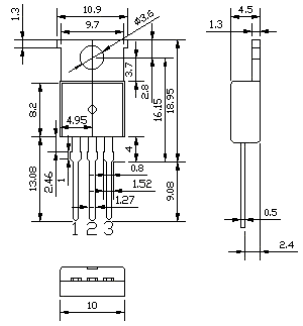
NPN EPITAXIAL SILICON DARLINGTON TRANSISTOR

…designed for use in horizontal output stages of video displays.

TO-220AB



1 : Base
2 : Collector (Heat Sink)
3 : Emitter

Weight: 1.9g Unit in mm

MAXIMUM RATINGS (T_C = 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	330	V
Collector Emitter Voltage	V_{CEO}	150	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	8	A
Collector Current (Pulse)	I_{CP}*	15	A
Base Current	I_B	2	A
Collector Dissipation T_C = 25 °C	P_C	60	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~150	°C

ELECTRICAL CHARACTERISTICS (T_C = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CES}	V_{CE} =330V, V_{BE} =0	-	-	100	μA
Collector Cutoff Current	I_{CEV}	V_{CE} =330V, V_{BE} =-6V	-	-	100	μA
Emitter Cutoff Current	I_{EBO}	V_{BE} =6V, I_C =0	-	-	3	mA
*Collector Emitter Saturation Voltage	$V_{CE(sat)}$	I_B =50mA, I_C =5A	-	-	1.5	V
*Base Emitter Saturation Voltage	$V_{BE(sat)}$	I_B =50mA, I_C =5A	-	-	2.4	V
*Collector Emitter Sustaining Voltage	$V_{CEO(sus)}$	I_B =0, I_C =100mA	150	-	-	V
*Damper Diode Forward Voltage	V_F	I_F =4A	-	-	2	V

*Pulsed: pulsed duration = 300μs, duty cycle = 1.5%

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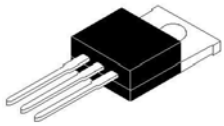

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